BC858

Rev.E Mar.-2016

描述 / Descriptions

SOT-23 塑封封装 PNP 半导体三极管。Silicon PNP transistor in a SOT-23 Plastic Package.

特征 / Features

高电流增益，低 $V_{CE(sat)}$。

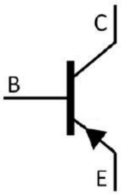
High current gain, Low collector-emitter saturation voltage.

用途 / Applications

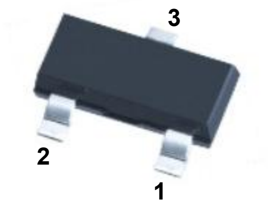
用于一般放大。

General power amplifier application.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1：Emitter　　PIN 2：Base　　PIN 3：Collector

放大及印章代码 / h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	A	B	C
h_{FE} Range	125～250	220～475	420～800
Marking	H3J	H3K	H3L

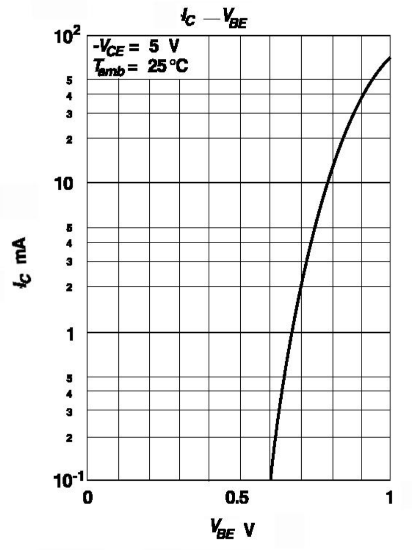
极限参数 / Absolute Maximum Ratings(Ta=25℃)

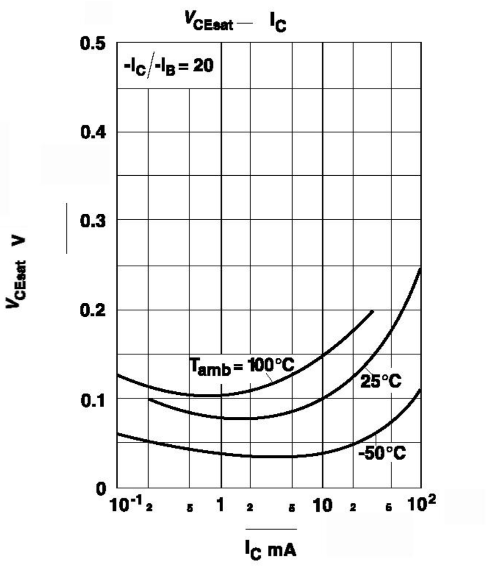
参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	-30	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55～150	℃

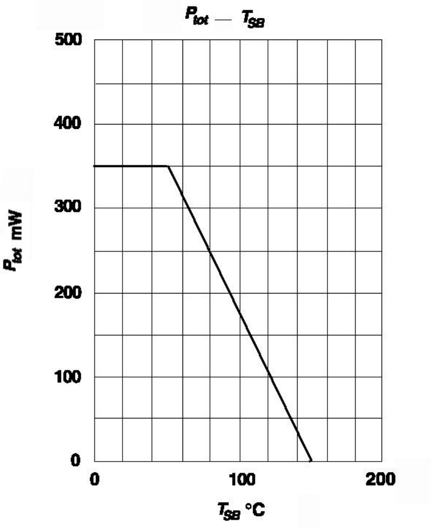
电性能参数 / Electrical Characteristics(Ta=25℃)

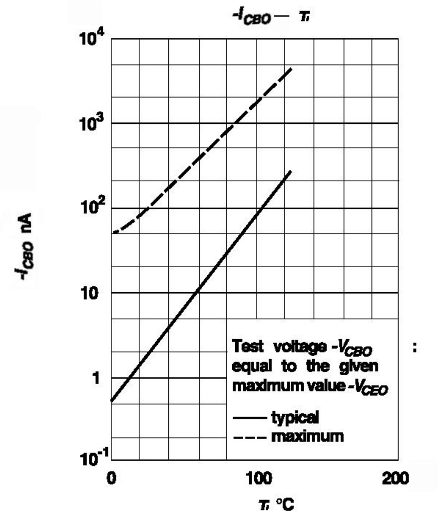
参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=-30 V I_E=0			-0.015	μA
DC Current Gain	h_{FE}	V_{CE}=-5.0V I_C=-2.0mA	125		800	
Collector to Emitter Saturation Voltage	$V_{CE(sat)(1)}$	I_C=-10mA I_B=-0.5mA		-0.09	-0.3	V
	$V_{CE(sat)(2)}$	I_C=-100mA I_B=-5.0mA		-0.25	-0.65	V
Base to Emitter Saturation Voltage	$V_{BE(sat)(1)}$	I_C=-10mA I_B=-0.5mA		-0.7		V
	$V_{BE(sat)(2)}$	I_C=-100mA I_B=-5.0mA		-0.9		V
Base to Emitter Voltage	$V_{BE(ON)(1)}$	V_{CE}=-5.0V I_C=-2.0mA	-0.6	-0.65	-0.75	V
	$V_{BE(ON)(2)}$	V_{CE}=-5.0V I_C=-10mA			-0.82	V
Transition Frequency	f_T	V_{CE}=-5.0V I_C=-10mA f=100MHz		150		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V I_E=0 f=1.0MHz		4.5		pF
Noise Figure	NF	V_{CE}=-6.0V I_C=-0.2mA R_g=2KΩ f=1.0KHz		2.0	10	dB

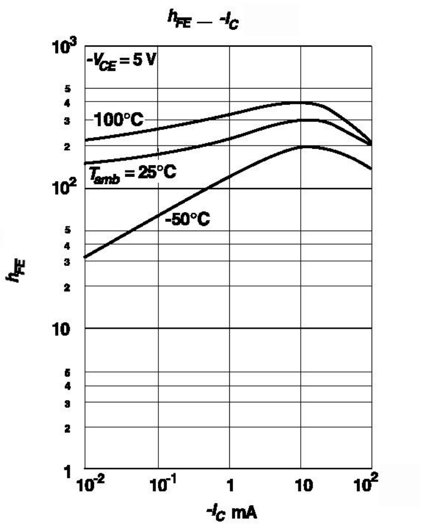
电参数曲线图 / Electrical Characteristic Curve

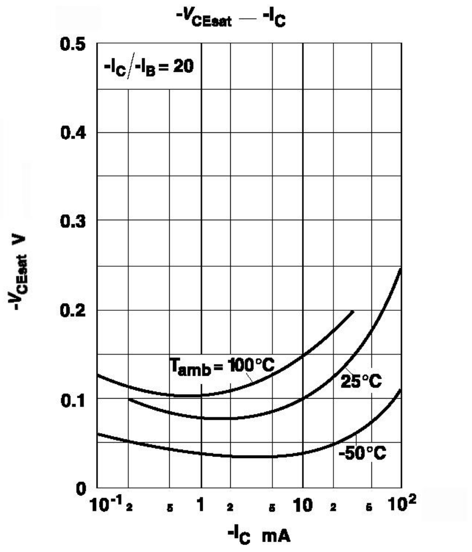






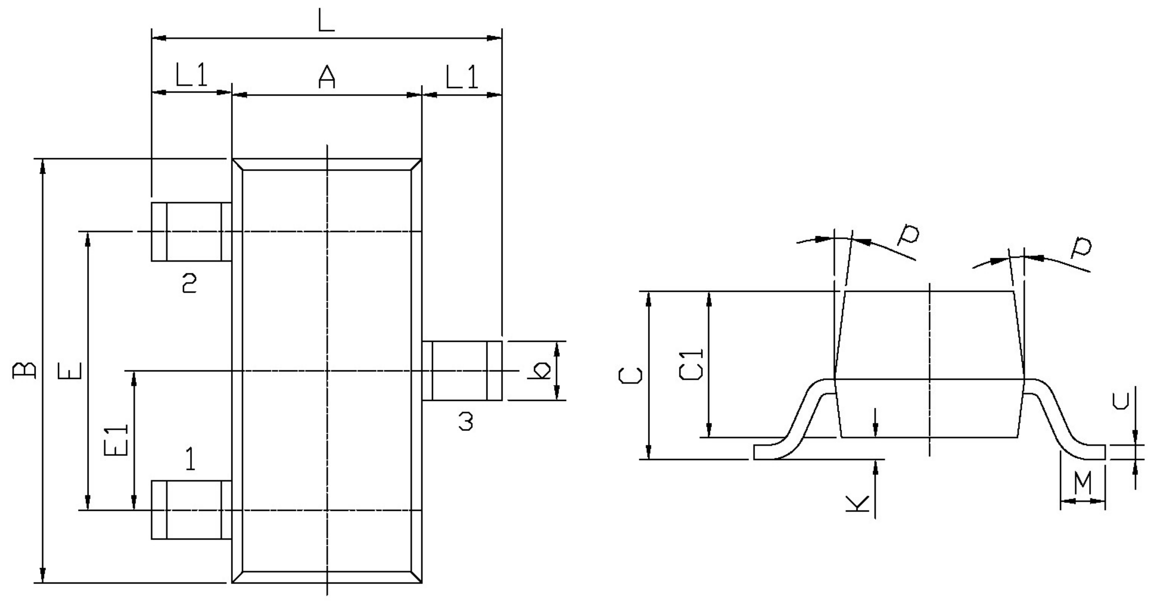






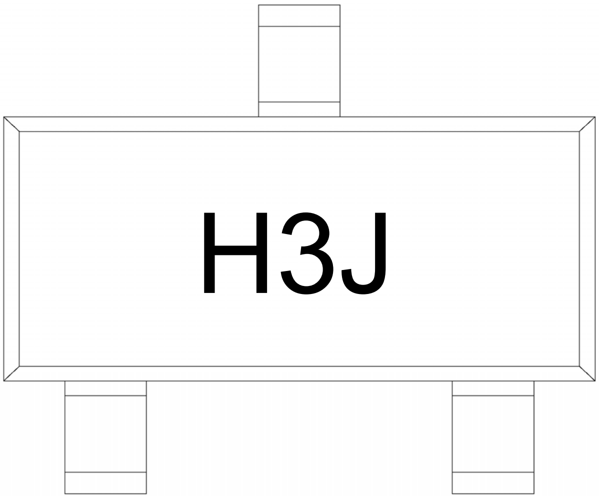
外形尺寸图 / Package Dimensions

SOT-23　　单位：mm



Symbol	Dimensions In Millmeters		Symbol	Dimensions In Millmeters	
	Min	Max		Min	Max
L	2.2	2.7	C	1.30Max	
L1	0.45	0.65	C1	0.90	1.20
A	1.15	1.50	c	0.05	0.20
B	2.70	3.10	K	0	0.10
E	1.70	2.10	M	0.20MIN	
E1	0.85	1.05	P	7°	
b	0.35	0.55			

印章说明 / Marking Instructions



说明：

H：　为公司代码

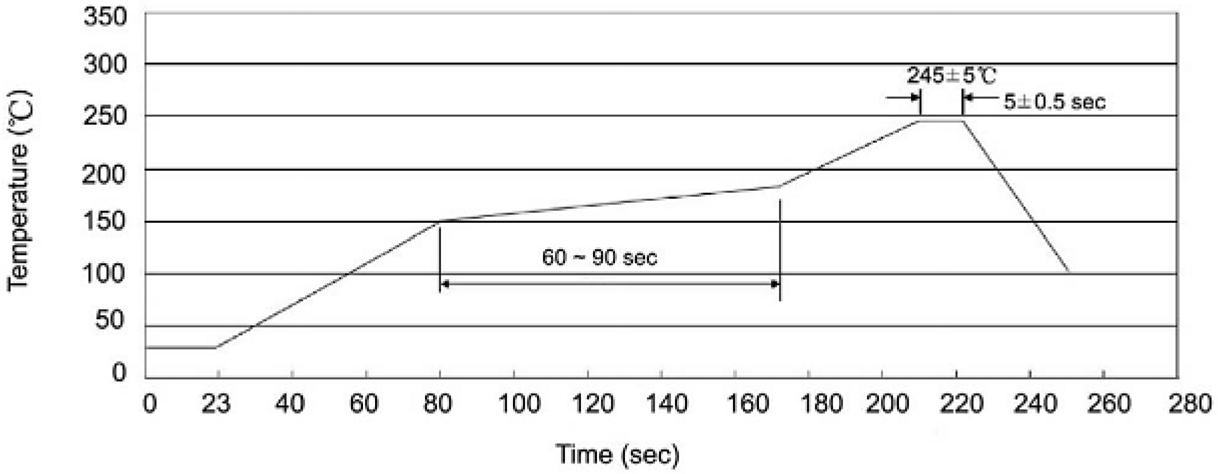
3J：　为型号代码

Note:

H:　Company Code

3J:　Product Type Code

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：	Note:
1、预热温度 25 ~ 150℃，时间 60 ~ 90sec;	1.Preheating:25~150℃, Time:60~90sec.
2、峰值温度 245±5℃，时间持续为 5±0.5sec;	2.Peak Temp.:245±5℃, Duration:5±0.5sec.
3、焊接制程冷却速度为 2 ~ 10℃/sec.	3. Cooling Speed: 2~10℃/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5℃　　时间：10±1 sec.　　Temp.:260±5℃　　Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	8	240,000	7″ ×8	180×120×180	385×257×392

使用说明 / Notices